

# 2MBI400VD-120-50

IGBT Modules

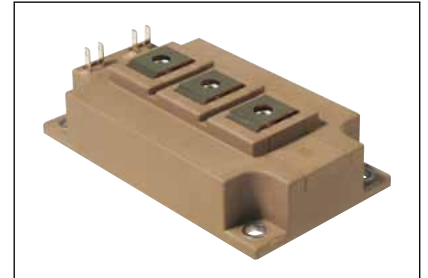
## IGBT MODULE (V series) 1200V / 400A / 2 in one package

### ■ Features

- High speed switching
- Voltage drive
- Low Inductance module structure

### ■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply
- Industrial machines, such as Welding machines



### ■ Maximum Ratings and Characteristics

#### ● Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items	Symbols	Conditions	Maximum ratings	Units
Collector-Emitter voltage	V <sub>CEs</sub>		1200	V
Gate-Emitter voltage	V <sub>GES</sub>		±20	V
Inverter	Collector current	Continuous	Tc=100°C Tc=25°C	400 520
		Ic pulse	1ms	800
	-Ic		400	
	-Ic pulse	1ms	800	
	Collector power dissipation	Pc	1 device	3330
Junction temperature	Tj		175	°C
Operating junction temperature (under switching conditions)	Tjop		150	
Case temperature	Tc		125	
Storage temperature	Tstg		-40 ~ +125	
Isolation voltage	V <sub>iso</sub>	AC : 1min.	2500	VAC
Screw torque	Mounting (*2)		6.0	N m
	Terminals (*3)		5.0	

Note \*1: All terminals should be connected together during the test.

Note \*2: Recommendable Value : 3.0-6.0 Nm (M5 or M6)

Note \*3: Recommendable Value : 2.5-5.0 Nm (M6)

#### ● Electrical characteristics (at Tj= 25°C unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Zero gate voltage collector current	I <sub>CEs</sub>	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 1200V	-	-	2.0	mA	
Gate-Emitter leakage current	I <sub>GES</sub>	V <sub>CE</sub> = 0V, V <sub>GE</sub> = ±20V	-	-	400	nA	
Gate-Emitter threshold voltage	V <sub>GE(th)</sub>	V <sub>CE</sub> = 20V, I <sub>c</sub> = 400mA	6.0	6.5	7.0	V	
Inverter	Collector-Emitter saturation voltage	V <sub>GE</sub> = 15V I <sub>c</sub> = 400A	V <sub>CE(sat)</sub> (terminal)	Tj=25°C	-	1.95	2.40
				Tj=125°C	-	2.25	-
	V <sub>CE(sat)</sub> (chip)	Tj=150°C	-	2.30	-		
		Tj=25°C	-	1.75	2.15		
		Tj=125°C	-	2.05	-		
Input capacitance	C <sub>ies</sub>	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0V, f = 1MHz	-	36.4	-	nF	
Turn-on time	ton	V <sub>CC</sub> = 600V	-	0.60	-	μs	
	tr	I <sub>c</sub> = 400A	-	0.20	-		
	tr(i)	V <sub>GE</sub> = ±15V	-	0.05	-		
Turn-off time	toff	R <sub>θ</sub> = 1Ω	-	0.80	-	μs	
	tf	Tj = 150°C	-	0.08	-		
Forward on voltage	V <sub>F</sub> (terminal)	V <sub>GE</sub> = 0V I <sub>F</sub> = 400A	Tj=25°C	-	1.85	2.30	
			Tj=125°C	-	2.00	-	
	V <sub>F</sub> (chip)	Tj=150°C	-	1.95	-		
		Tj=25°C	-	1.70	2.15		
		Tj=125°C	-	1.85	-		
Reverse recovery time	trr	I <sub>F</sub> = 400A	-	0.15	-	μs	

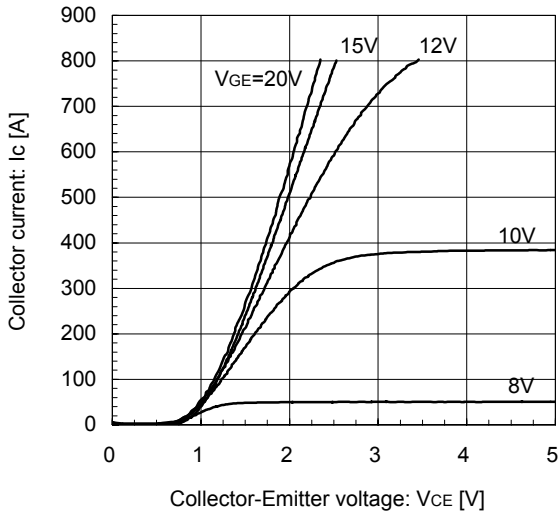
#### ● Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance (1device)	R <sub>th(j-c)</sub>	IGBT FWD	-	-	0.045	°C/W
Contact thermal resistance (1device) (*4)	R <sub>th(c-f)</sub>	with Thermal Compound	-	0.013	-	

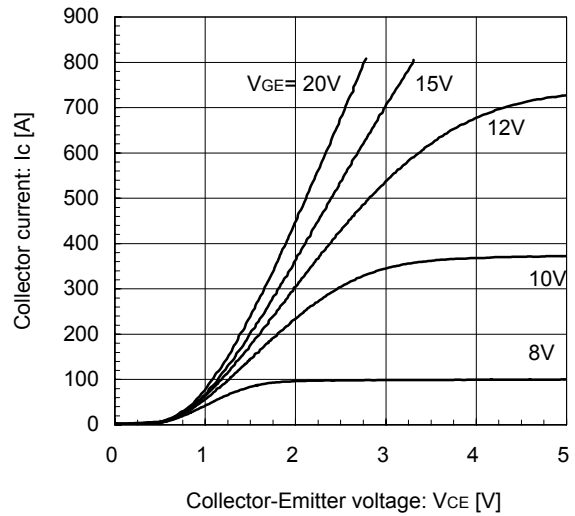
Note \*4: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

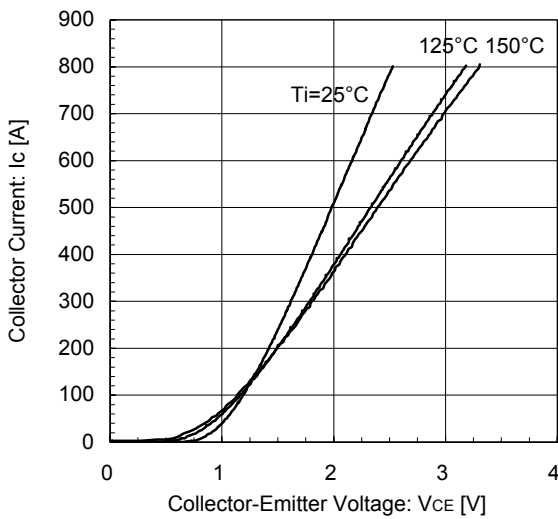
Collector current vs. Collector-Emitter voltage (typ.)  
T<sub>j</sub> = 25°C / chip



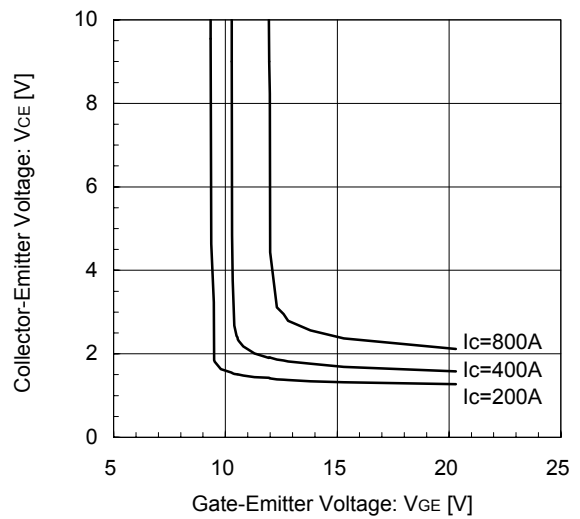
Collector current vs. Collector-Emitter voltage (typ.)  
T<sub>j</sub> = 150°C / chip



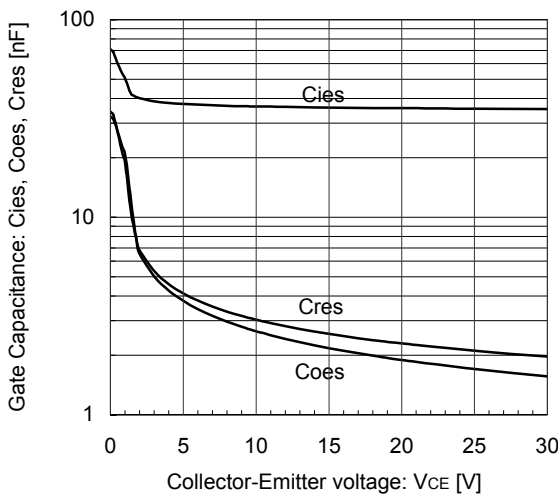
Collector current vs. Collector-Emitter voltage (typ.)  
V<sub>GE</sub> = 15V / chip



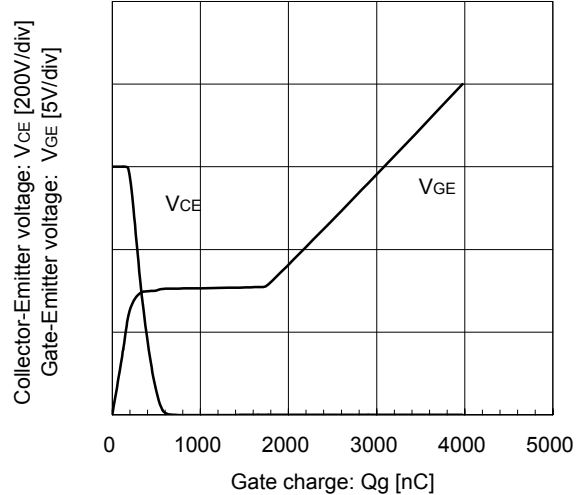
Collector-Emitter voltage vs. Gate-Emitter voltage  
T<sub>j</sub> = 25°C / chip



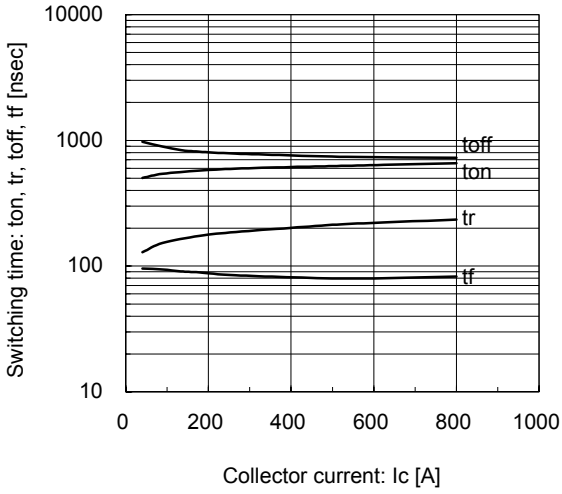
Gate Capacitance vs. Collector-Emitter Voltage  
V<sub>GE</sub> = 0V, f = 1MHz, T<sub>j</sub> = 25°C



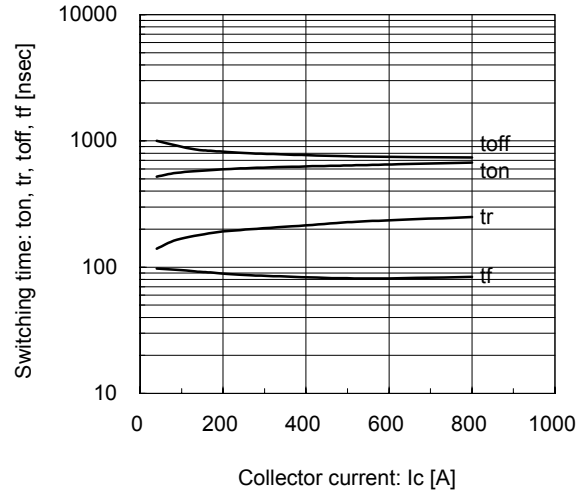
Dynamic Gate Charge (typ.)  
V<sub>CC</sub> = 600V, I<sub>c</sub> = 400A, T<sub>j</sub> = 25°C



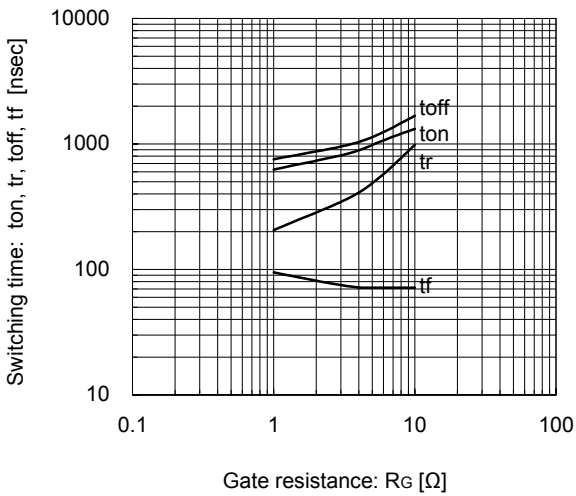
Switching time vs. Collector current (typ.)  
 $V_{CC}=600V, V_{GE}=\pm 15V, R_G=1\Omega, T_j=125^\circ C$



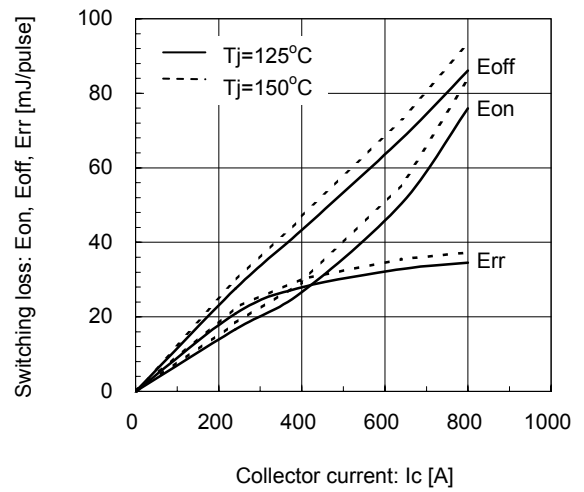
Switching time vs. Collector current (typ.)  
 $V_{CC}=600V, V_{GE}=\pm 15V, R_G=1\Omega, T_j=150^\circ C$



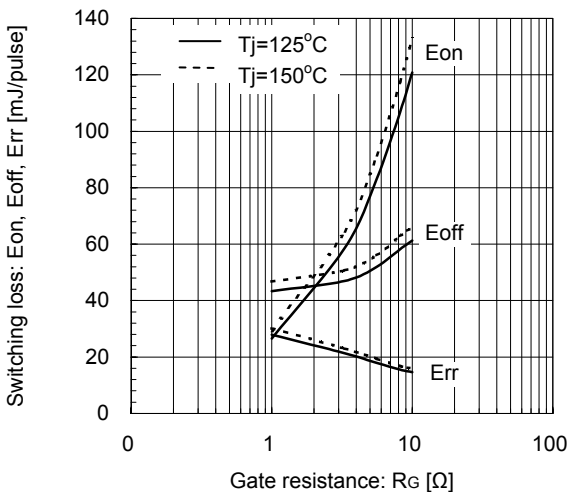
Switching time vs. Gate resistance (typ.)  
 $V_{CC}=600V, I_c=400A, V_{GE}=\pm 15V, T_j=125^\circ C$



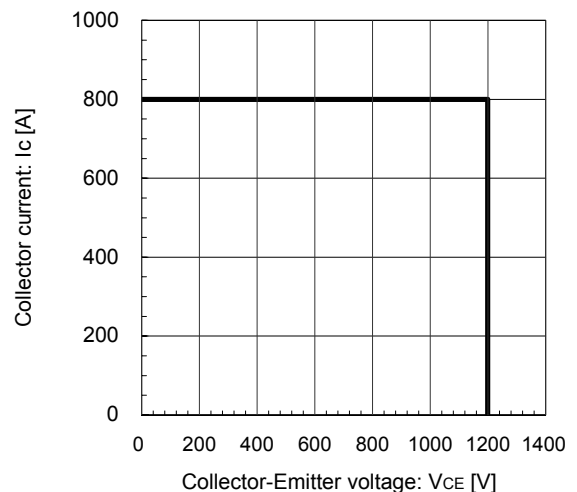
Switching loss vs. Collector current (typ.)  
 $V_{CC}=600V, V_{GE}=\pm 15V, R_G=1\Omega, T_j=125^\circ C, 150^\circ C$



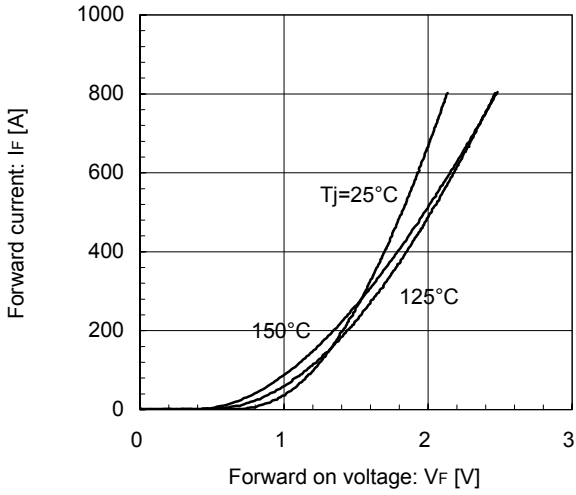
Switching loss vs. Gate resistance (typ.)  
 $V_{CC}=600V, I_c=400A, V_{GE}=\pm 15V, T_j=125^\circ C, 150^\circ C$



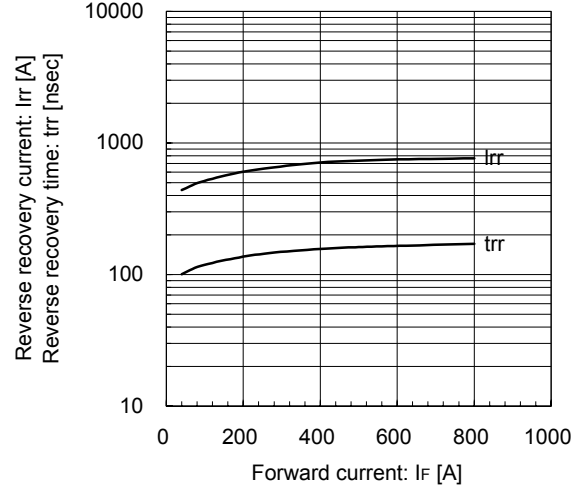
Reverse bias safe operating area (max.)  
 $+V_{GE}=15V, -V_{GE}=15V, R_G=1\Omega, T_j=150^\circ C$



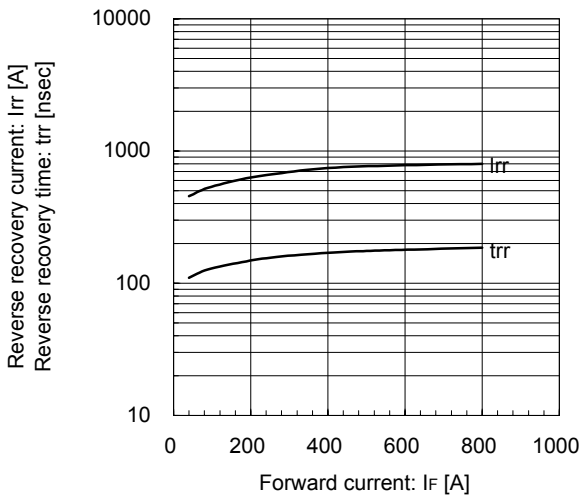
Forward Current vs. Forward Voltage (typ.)  
chip



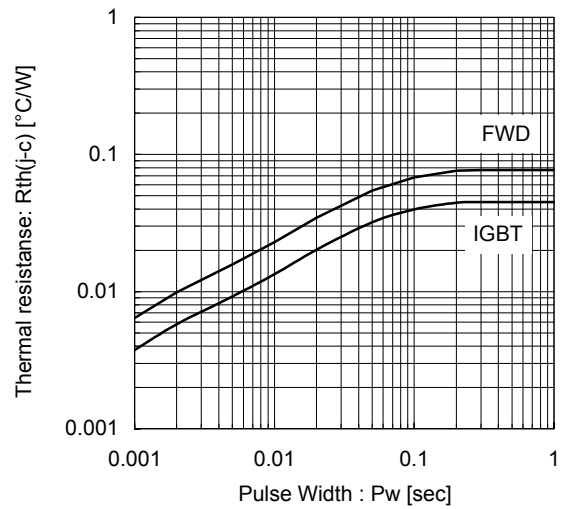
Reverse Recovery Characteristics (typ.)  
Vcc=600V, VGE=±15V, RG=1Ω, Tj=125°C



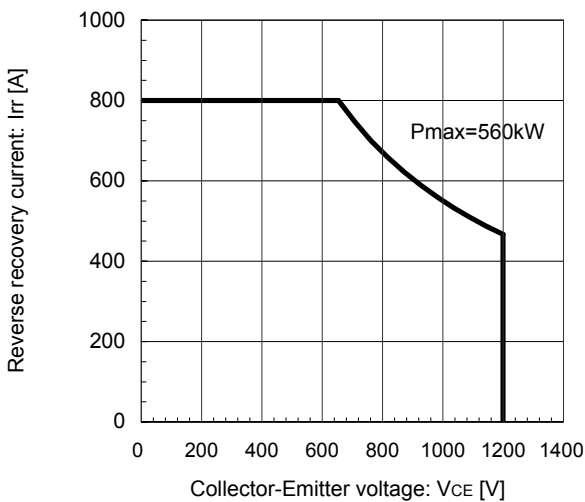
Reverse Recovery Characteristics (typ.)  
Vcc=600V, VGE=±15V, RG=1Ω, Tj=150°C



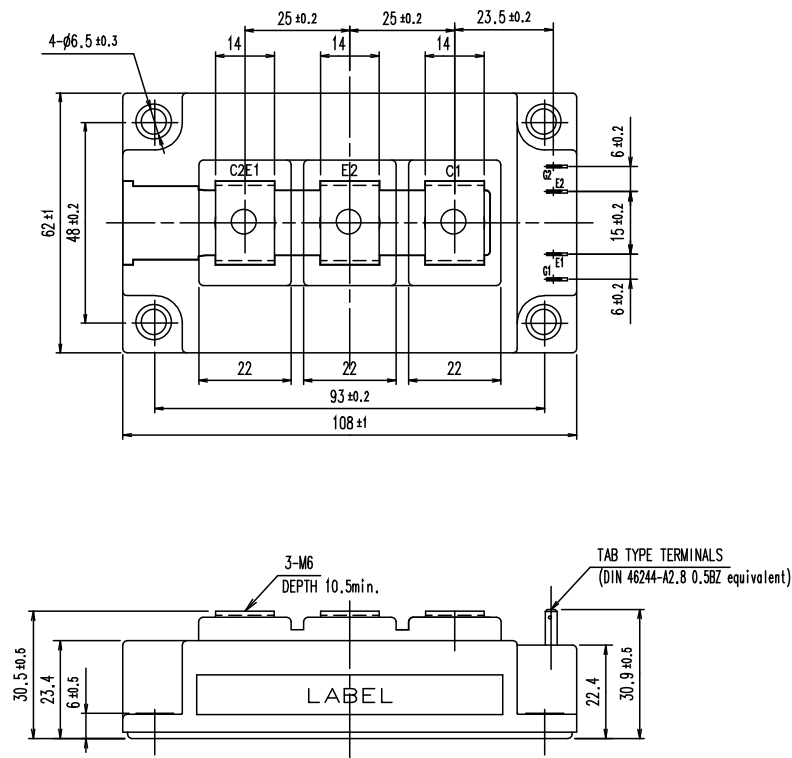
Transient Thermal Resistance (max.)



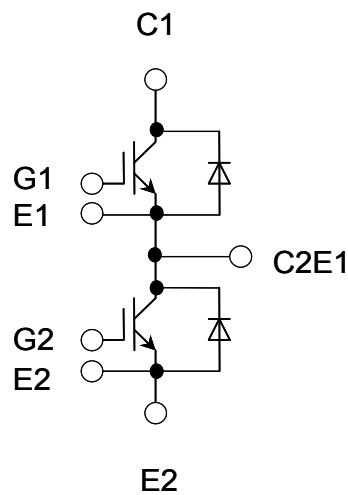
FWD safe operating area (max.)  
Tj=150°C



■ Outline Drawings, mm



■ Equivalent Circuit Schematic



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